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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/497,508	02/04/2000	Jin Jang	8733.20079	7572	
30827 75	30827 7590 04/20/2005			EXAMINER	
MCKENNA LONG & ALDRIDGE LLP			LOUIE, W	LOUIE, WAI SING	
1900 K STREE WASHINGTON			ART UNIT	ART UNIT PAPER NUMBER	
,			2814		
			DATE MAILED: 04/20/2009	5	

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)				
Office Action Summary		09/497,508	JANG ET AL.	JANG ET AL.			
		Examiner	Art Unit				
		Wai-Sing Louie	2814	λ,			
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply							
A SH THE - Exte after - If the - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REPL MAILING DATE OF THIS COMMUNICATION. nsions of time may be available under the provisions of 37 CFR 1. SIX (6) MONTHS from the mailing date of this communication. period for reply specified above is less than thirty (30) days, a rep or period for reply is specified above, the maximum statutory period are to reply within the set or extended period for reply will, by statutively received by the Office later than three months after the mailing patent term adjustment. See 37 CFR 1.704(b).	136(a). In no event, however, m ly within the statutory minimum o will apply and will expire SIX (6) e, cause the application to becor	ay a reply be timely filed of thirty (30) days will be considered timel MONTHS from the mailing date of this c ne ABANDONED (35 U.S.C. § 133).				
Status							
2a)⊠	Responsive to communication(s) filed on <u>01 February 2005</u> . This action is FINAL. 2b) This action is non-final. Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Disposition of Claims							
 4) Claim(s) 9-19 is/are pending in the application. 4a) Of the above claim(s) 14-19 is/are withdrawn from consideration. 5) Claim(s) is/are allowed. 6) Claim(s) 9-13 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or election requirement. 							
Applicat	ion Papers			•			
9) The specification is objected to by the Examiner. 10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner. Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a). Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d). 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.							
Priority under 35 U.S.C. § 119							
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 							
2) Notice 3) Infor	et(s) ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08 cr No(s)/Mail Date	Paper) 5) Notice	iew Summary (PTO-413) No(s)/Mail Date e of Informal Patent Application (PTo :	O-152)			

DETAILED ACTION

Applicant withdraws claims 14-19, in the reply filed on 2/1/05 is acknowledge. It is suggested that non-elected claims 14-19 be canceled in the response to this Office Action.

Claim Rejections - 35 USC § 112

The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

Claims 9-13 are rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention.

• "The polycrystalline silicon film comprising a uniform distribution of needle-shaped crystallites" is new matter. The specification discloses "the whole amorphous silicon is crystallized uniformly" and "a bar-like shape and the whole amorphous silicon is crystallized uniformly" (page 9).

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Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 9-13 are rejected under 35 U.S.C. 103(a) as being unpatentable over Miyanaga et al. (US 5,932,893) in view of Fonash et al. (US 5,994,164).

With regard to claim 9, Miyanaga et al. disclose a semiconductor device having doped polycrystalline layer (col. 11, line 8 to col. 21, line 45) comprising:

- Containing metal atoms, nickel, having a density range of 1x10¹⁷ to 1x10²⁰ atoms/cm³ on average, where the metal is a catalyst for metal induced crystallization of amorphous silicon (col. 8, lines 41-60, col. 11, lines 44-46 and fig. 4);
- The polycrystalline silicon film 104 is formed on an insulating substrate 101 (col.
 11, lines 51-63);
- The polycrystalline silicon film comprises an uniform distribution of the crystallites is needle-like (col. 6, lines 1-3; col. 7, lines 31-35; and col. 18, line 62 to col. 19, line 10);
- Miyanaga et al. do not disclose electrical conductivity activation energy between
 0.52 to 0.71 eV. However, Fonash et al. disclose forming a polycrystalline film with nickel as a catalyst element at low temperature annealing (Fonash col. 3, lines 38-49), where the conductivity activation energy is 0.52 eV @ 290°C

(Fonash fig. 8b). Therefore, it would have been obvious in light of the teaching of Fonash et al. that the claimed activation energy is achieved when polycrystalline film has nickel as catalyst. Since the applicant has not established the criticality of the activation energy stated and since these values are in common use in similar devices in the art, it would have been obvious to one of ordinary skill in the art to use these values in the device. Where patentability is said to be based upon particular chosen dimension or upon another variable recited in a claim, the applicant must show that the chosen dimensions are critical. In re Woodruff, 919 F2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990).

With regard to claim 10, Miyanaga et al. disclose the metal is nickel (col. 11, lines 44-50).

With regard to claim 11, Miyanaga et al. disclose the metal works as a catalyst during crystallization (col. 11, line 11).

With regard to claim 12, Miyanaga et al. disclose a insulating (buffer) layer 102 between the substrate 101 and the crystalline (polycrystalline) silicon film 104 (fig. 1a).

With regard to claim 13, Miyanaga et al. disclose the needle-shaped silicon crystallites are formed by migration (movement) of a silicide of the metal (col. 7, lines 31-35 and col. 11, lines 44-46).

Response to Arguments

Applicant's arguments filed 8/23/2004 have been fully considered but they are not persuasive:

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Applicant argues that Miyanaga et al. do not teach or suggest an uniform distribution of needle-shaped silicon crystallites". However, Miyanaga et al. disclose the crystallization to a uniform concentration gradient (col. 6, lines 1-3) and crystal growth is needle-like in an uniform direction (col. 18, line 62 to col. 19, line 10).
 Therefore, Miyanaga et al. meet the limitation.

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Conclusion

THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Wai-Sing Louie whose telephone number is (571) 272-1709. The examiner can normally be reached on 7:30 AM to 4:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (571) 272-1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

April 13, 2005.